

PNP MJ4030 - MJ4031 - MJ4032

MEDIUM POWER COMPLEMENTARY SILICON TRANSISTORS

They are silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case.

They are intented for use as output devices in complementary general purpose amplifier applications.

The complementary NPN types are the MJ4033, MJ4034, MJ4035 Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit		
			MJ4030	-60		
V _{CBO}	Collector-Base Voltage	I _E =0	MJ4031	-80	V	
	-		MJ4032	-100		
			MJ4030	-60		
V _{CEO}	Collector-EmitterVoltage	I _B =0	MJ4031	-80	V	
			MJ4032	-100		
			MJ4030			
V _{EBO}	Emitter-Base Voltage	I _C =0	MJ4031	-5.0	V	
			MJ4032			
I _C	Collector Current			-16	А	
I _B	Base Current			-0.5	А	
Ρτ	Power Dissipation	@ T _C < 25°		150	W	
TJ	Junction Temperature			200	°C	
Ts	Storage Temperature			-65 to +200		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-C}	Thermal Resistance, Junction to Case1.17°C/		°C/W



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition	on(s)	Min	Тур	Max	Unit
	Collector Emitter		MJ4030	-60	-	-	
V _{CEO}	Collector-Emitter Voltage (*)	I _C =-100 mA, I _B =0	MJ4031	-80	-	-	V
			MJ4032	-100			
	Collector Cutoff Current	V_{CE} =-30 Vdc, I _B =0	MJ4030	-	-		
I _{CEO}		V_{CE} =-40 Vdc, I _B =0	MJ4031	-	-	-3.0	mA
		V _{CE} =-50 V, I _B =0	MJ4032	-	-		
			MJ4030			-5.0	mA
I _{EBO}	Emitter Cutoff Current	V _{BE} =-5.0 V, I _C =0	MJ4031	-	-		
			MJ4032				
		V _{CB} =-60 V R _{BE} =1.0 kΩ	MJ4030	-	-	- 1.0	
		V_{CB} =-80 V R _{BE} =1.0 kΩ	MJ4031	-	-		
	Collector-Emitter Leakage Current	V_{CB} =-100 V R _{BE} =1.0 kΩ	MJ4032				mA
		V_{CB} =-60 V R _{BE} =1.0 kΩ T _C =150°C	MJ4030	-	-	-5.0	
		V _{CB} =-80 V R _{BE} =1.0 kΩ T _C =150°C	MJ4031	-	-		
		V _{CB} =-100 V R _{BE} =1.0 kΩ T _C =150°C	MJ4032				
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C =-10 A I _B =-40 mA	MJ4030 MJ4031 MJ4032	-	-	-2.5	
		I _C =-16 A I _B =-80 mA	MJ4032 MJ4030 MJ4031 MJ4032	-	-	-4.0	V
V _{BE}	Base-Emitter Voltage (*)	I _C =-10 A V _{CE} =-3.0V	MJ4030 MJ4031 MJ4032	-	-	-3	V
h _{FE}	DC Current Gain (*)	V _{CE} =-10 V I _C =-3.0 A	MJ4030 MJ4031 MJ4032	1000	-	-	-

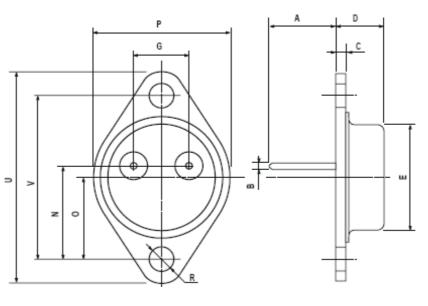
(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle $\angle~2.0\%$



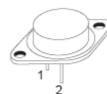
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)			
	min	max	
A	11	13.10	
В	0.97	1.15	
С	1.5	1.65	
D	8.32	8.92	
F	19	20	
G	10.70	11.1	
N	16.50	17.20	
Р	25	26	
R	4	4.09	
U	38.50	39.30	
V	30	30.30	



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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